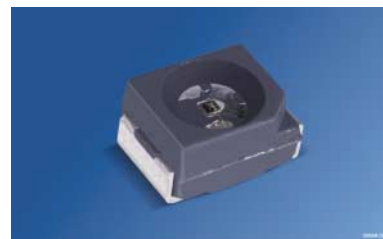


Rote Lumineszenzdiode

Red Emitter

Lead (Pb) Free Product - RoHS Compliant

SFH 4272



Wesentliche Merkmale

- Schwarz eingefärbtes TOPLED-Gehäuse
- Typische Emissionswellenlänge 645nm
- Verbesserte Abbildungseigenschaften durch Absorption der Seitenstrahlung
- Größe der Leuchtquelle 200µm x 200µm
- IR Reflow und TTW Löten geeignet
- Feuchte-Empfindlichkeitsstufe 2 nach JEDEC Standard J-STD-020A

Features

- Black coloured TOPLED-package
- Typical Peakwavelength 645nm
- Improved imaging characteristics due to absorption of side emission
- Size of emitting area 200µm x 200µm
- Suited for IR Reflow and TTW-soldering
- Moisture sensitivity level 2 according to JEDEC Standard J-STD-020A

Anwendungen

- Miniaturlichtschranken und Lichtschranken über große Entfernungen
- Industrieelektronik
- „Messen/Steuern/Regeln“
- Automobiltechnik
- Sensorik
- Alarm- und Sicherungssysteme
- IR-Freiraumübertragung

Applications

- Miniature and long distance photointerrupters
- Industrial electronics
- For drive and control circuits
- Automotive technology
- Sensor technology
- Alarm and safety equipment
- IR free air transmission

Typ Type	Bestellnummer Ordering Code	Strahlstärkegruppierung ¹⁾ ($I_F = 20 \text{ mA}$, $t_p = 20 \text{ ms}$) Radiant Intensity Grouping ¹⁾ $I_e \text{ (mW/sr)}$
SFH 4272	Q65110A2522	> 0.16 (typ. 0.35)

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.01 \text{ sr}$ / measured at a solid angle of $\Omega = 0.01 \text{ sr}$

Grenzwerte ($T_A = 25\text{ °C}$)

Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlassstrom Forward current	I_F	30	mA
Stoßstrom, $\tau = 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	1	A
Verlustleistung Power dissipation	P_{tot}	80	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm^2 Thermal resistance junction - ambient mounted on PC-board (FR4), padsize 16 mm^2 each	R_{thJA}	500	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	R_{thJS}	280	K/W

Kennwerte ($T_A = 25\text{ °C}$)

Characteristics

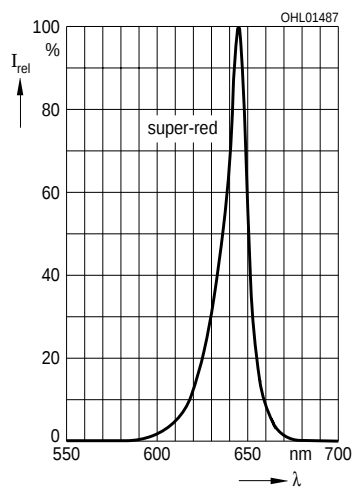
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$	λ_{peak}	645	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 20\text{ mA}$	$\Delta\lambda$	16	nm
Abstrahlwinkel Half angle	φ	± 60	Grad deg.
Aktive Chipfläche Active chip area	A	0.04	mm ²
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.2×0.2	mm
Durchlassspannung Forward voltage $I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$	V_F	$2.0 (\leq 2.5)$	V
Sperrstrom Reverse current $V_R = 5\text{ V}$	I_R	$0.01 (\leq 10)$	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	1	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 20\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 20\text{ mA}$	TC_I	-0.5	%/K
Temperaturkoeffizient von V_F , $I_F = 20\text{ mA}$ Temperature coefficient of V_F , $I_F = 20\text{ mA}$	TC_V	-2	mV/K
Temperaturkoeffizient von λ , $I_F = 20\text{ mA}$ Temperature coefficient of λ , $I_F = 20\text{ mA}$	TC_λ	$+0.14$	nm/K

Strahlstärke I_e in Achsrichtung (gemessen bei einem Raumwinkel $\Omega = 0.01\text{ sr}$)Radiant Intensity I_e in Axial Direction (at a solid angle of $\Omega = 0.01\text{ sr}$)

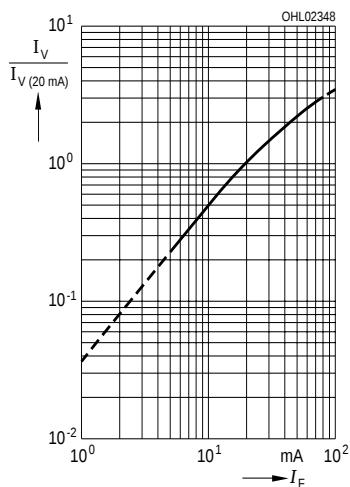
Bezeichnung Parameter	Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$	I_e	> 0.16 (typ. 0.35)	mW/sr

Relative Spectral Emission

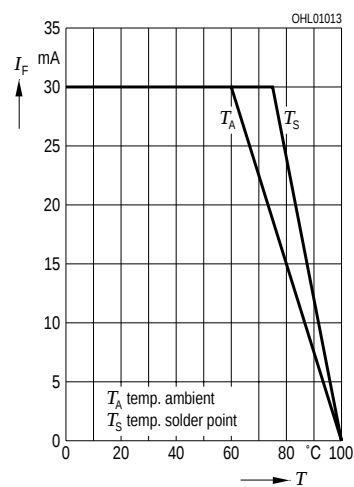
$$I_{\text{rel}} = f(\lambda)$$

**Radiant Intensity**

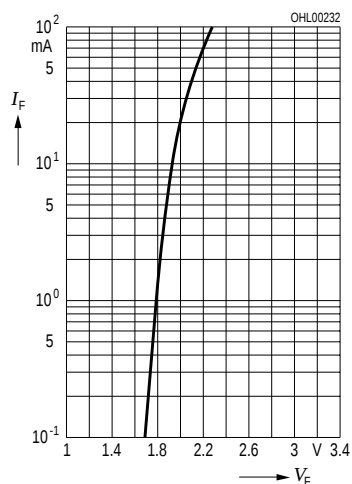
$$I_e/I_{e(20 \text{ mA})} = f(I_F)$$

**Max. Permissible Forward Current**

$$I_F = f(T_A)$$

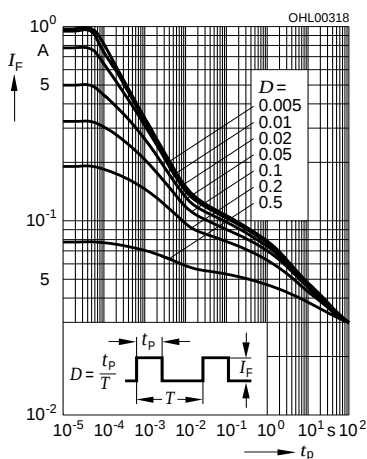
**Forward Current**

$$I_F = f(V_F) \text{ single pulse, } t_p = 20 \mu\text{s}$$

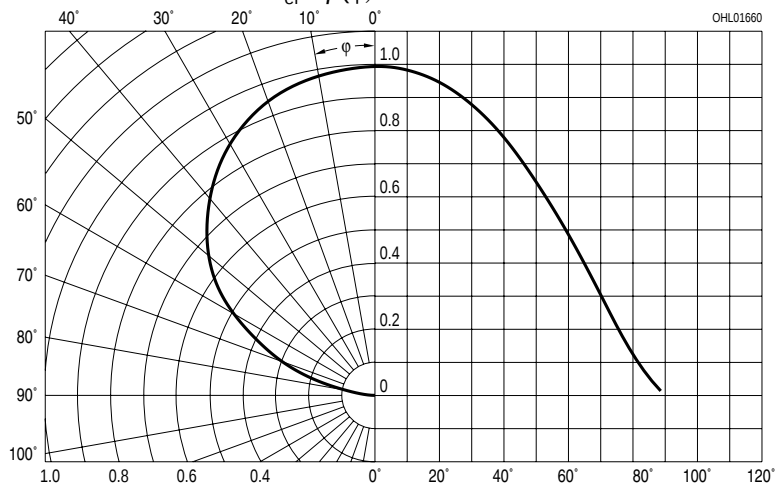
**Permissible Pulse Handling**

$$\text{Capability } I_F = f(t_p), T_A = 25^\circ\text{C}$$

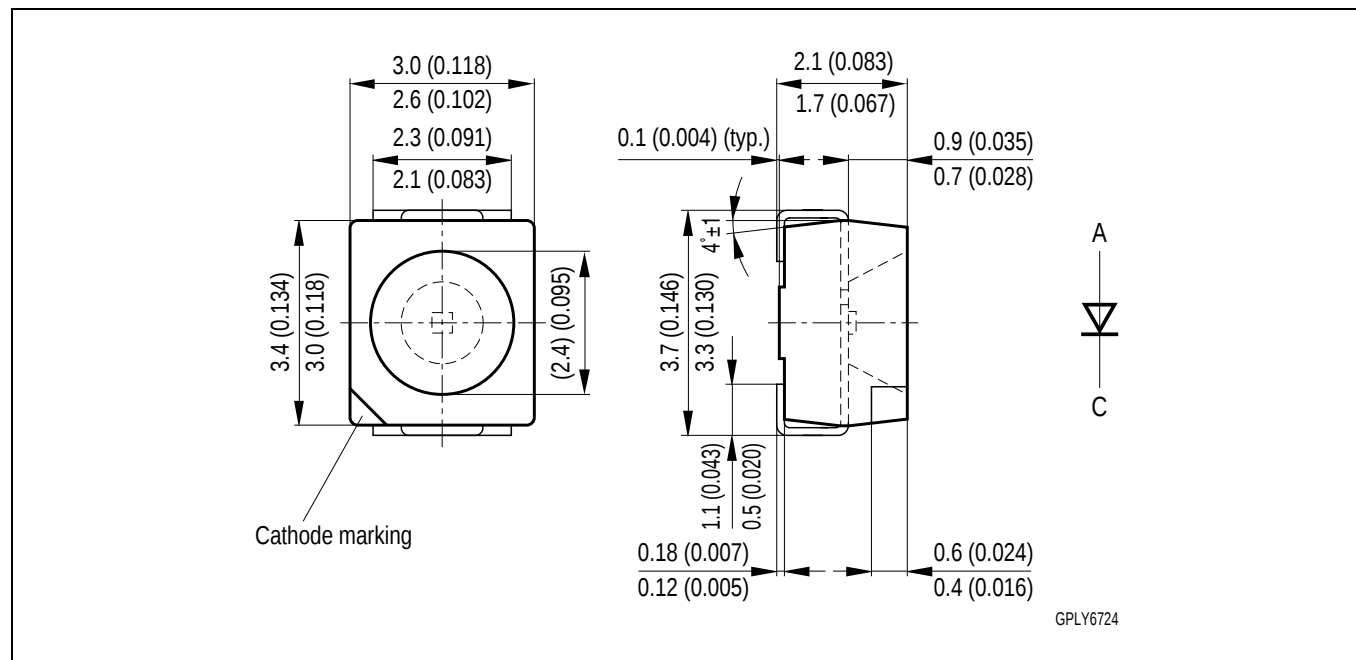
duty cycle $D = \text{parameter}$

**Radiation Characteristics**

$$S_{\text{el}} = f(\varphi)$$



Maßzeichnung Package Outlines

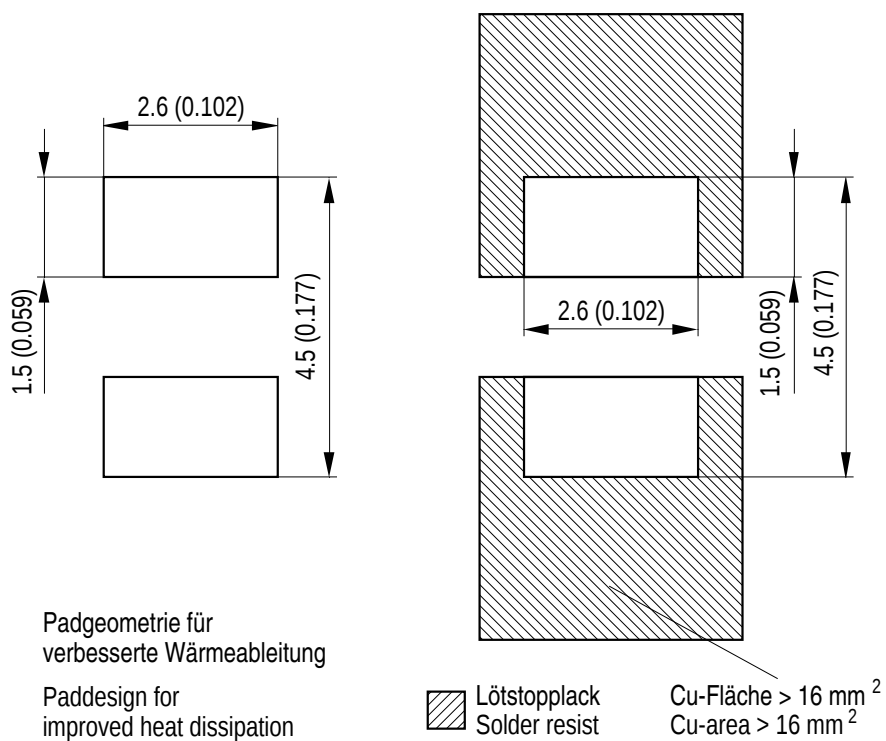


Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Gehäuse / Package	TOPLED®, klarer Verguss / TOPLED®, clear resin
Anschlussbelegung Pin configuration	abgeschrägte Ecke: Kathode beveled edge: Cathode
Farbe Color	schwarz black
Brechungsindex Verguss Refractive index resin	1.53 1.53

Empfohlenes Lötpaddesign
Recommended Solder Pad

IR-Reflow Löten
 IR Reflow Soldering



OHLPY970

Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch)
 Gehäuse für Wellenlöten (TTW) geeignet / Package suitable for TTW-soldering

Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

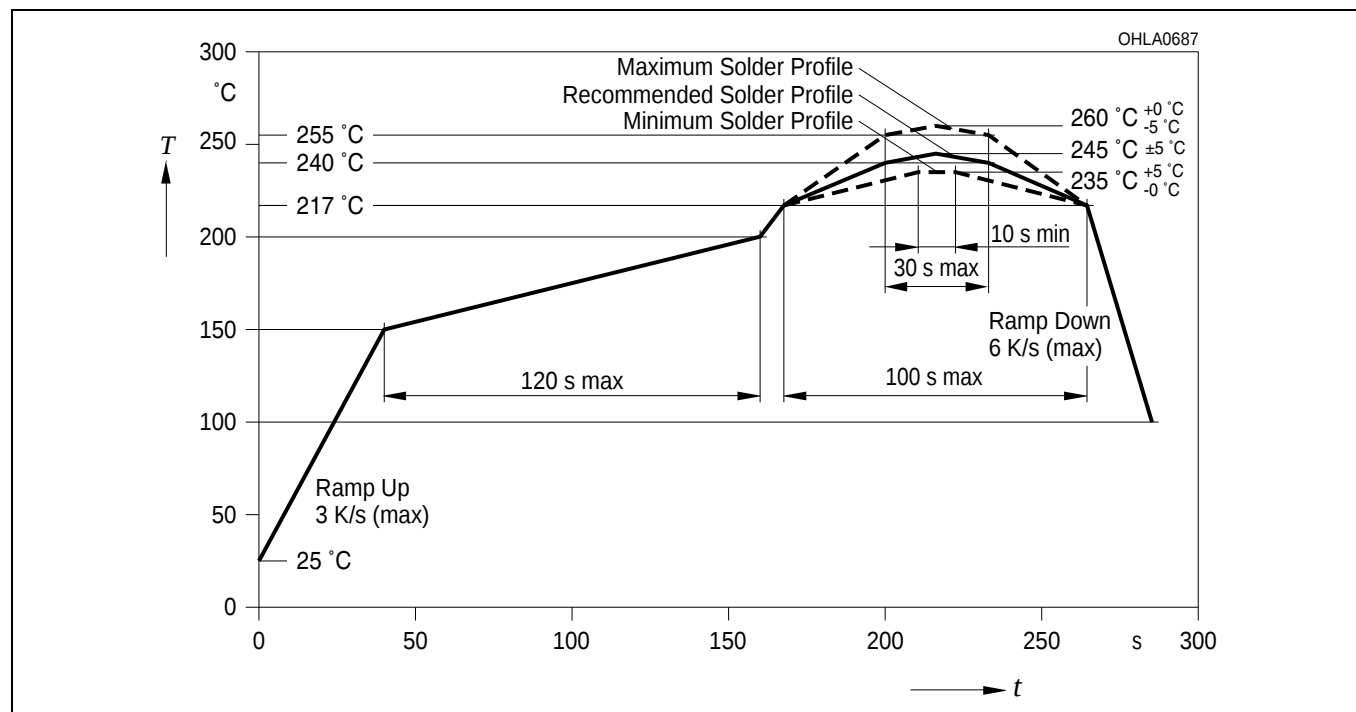
Lötbedingungen**Soldering Conditions****IR-Reflow Lötprofil für bleifreies Löt****IR Reflow Soldering Profile for lead free soldering**

Vorbehandlung nach JEDEC Level 2

Preconditioning acc. to JEDEC Level 2

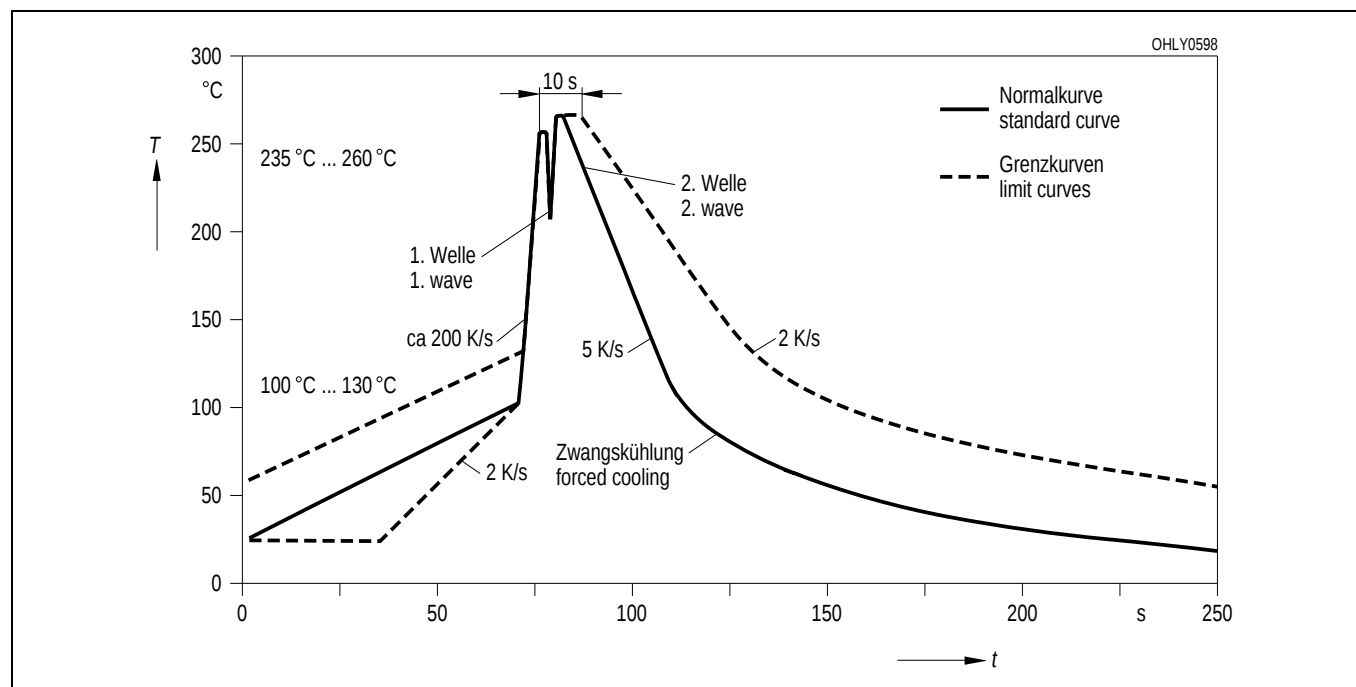
(nach J-STD-020B)

(acc. to J-STD-020B)

**Wellenlöt (TTW)****TTW Soldering**

(nach CECC 00802)

(acc. to CECC 00802)



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Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.